Electrical Characteristics @ Tj = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	400	—	—	V	V_{GS} = 0V, I_D = 1.0mA
$\Delta BV_{DSS}/\Delta T_J$	Temperature Coefficient of Breakdown Voltage	—	0.46	—	V/°C	Reference to 25°C, I_D = 1.0mA
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	—	—	0.20	Ω	V_{GS} = 10V, I_D = 14A ④
		—	—	0.23		V_{GS} = 10V, I_D = 23A
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
g_{fs}	Forward Transconductance	1.4	—	—		V_{DS} = 15V, I_{DS} = 14A ④
I_{DSS}	Zero Gate Voltage Drain Current	—	—	25	μA	V_{DS} = 320V ,V_{GS}=0V
		—	—	250		V_{DS} = 320V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V_{GS} = 20V
I_{GSS}	Gate-to-Source Leakage Reverse	—	—	-100		V_{GS} = -20V
Q_g	Total Gate Charge	—	—	210	nC	V_{GS} =10V, I_D = 23A
Q_{gs}	Gate-to-Source Charge	—	—	28		V_{DS} = 200V
Q_{gd}	Gate-to-Drain ('Miller') Charge	—	—	120		
$t_{d(on)}$	Turn-On Delay Time	—	—	33	ns	V_{DD} = 200V, I_D = 23A,
t_r	Rise Time	—	—	140		V_{GS} =10V, R_G = 2.35Ω
$t_{d(off)}$	Turn-Off Delay Time	—	—	120		
t_f	Fall Time	—	—	99		
$L_S + L_D$	Total Inductance	—	6.8	—	nH	Measured from drain lead (6mm/ 0.25in. from package) to source lead (6mm/0.25in. from package)
C_{iss}	Input Capacitance	—	4200	—	pF	V_{GS} = 0V, V_{DS} = 25V
C_{oss}	Output Capacitance	—	900	—		f = 1.0MHz
C_{rss}	Reverse Transfer Capacitance	—	400	—		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	23	A	
I_{SM}	Pulse Source Current (Body Diode) ①	—	—	92		
V_{SD}	Diode Forward Voltage	—	—	1.8	V	T_j = 25°C, I_S = 23A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	—	—	1000	nS	T_j = 25°C, I_F = 23A, di/dt ≤ 100A/μs
Q_{RR}	Reverse Recovery Charge	—	—	16	μC	V_{DD} ≤ 50V ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R_{thJC}	Junction-to-Case	—	—	0.5	°C/W	
R_{thCS}	Csae-to-sink	—	0.21	—		
R_{thJA}	Junction-to-Ambient	—	—	48		Typical socket mount

Note: Corresponding Spice and Saber models are available on International Rectifier Website.

For footnotes refer to the last page

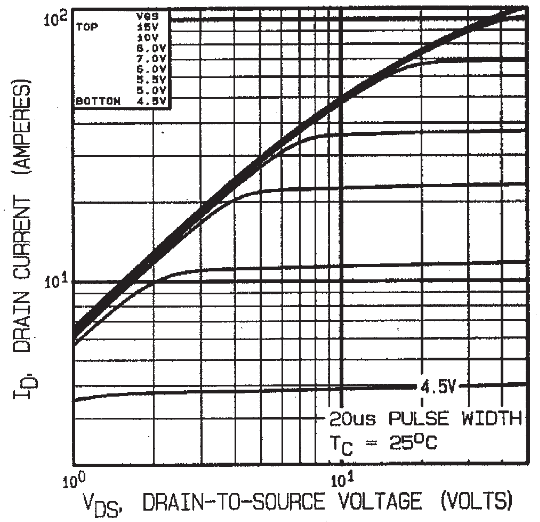


Fig 1. Typical Output Characteristics

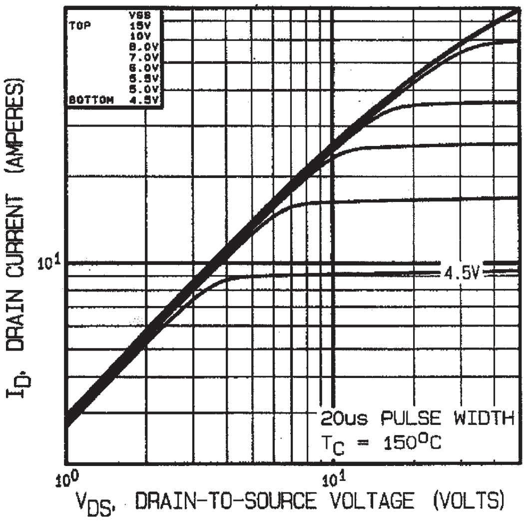


Fig 2. Typical Output Characteristics

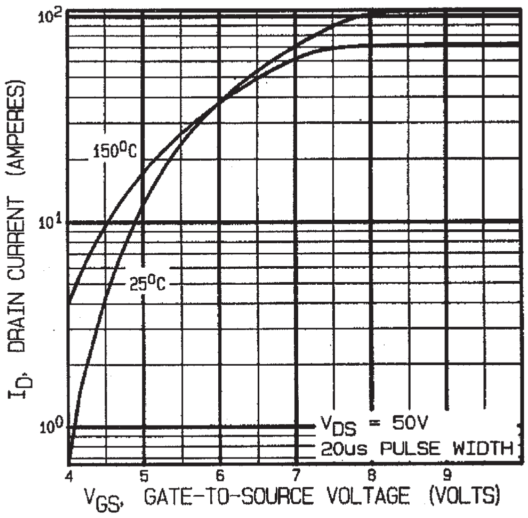


Fig 3. Typical Transfer Characteristics

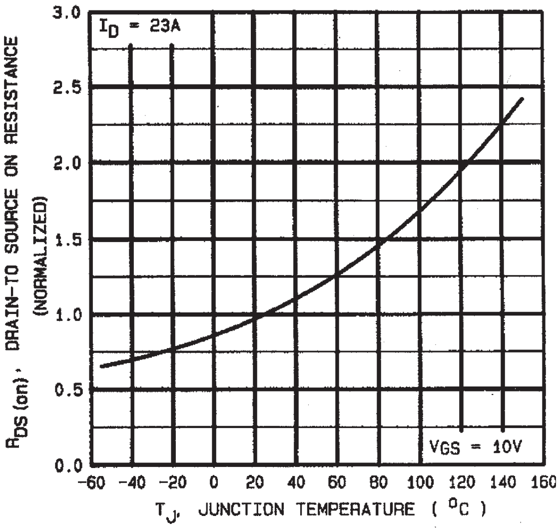


Fig 4. Normalized On-Resistance
Vs. Temperature

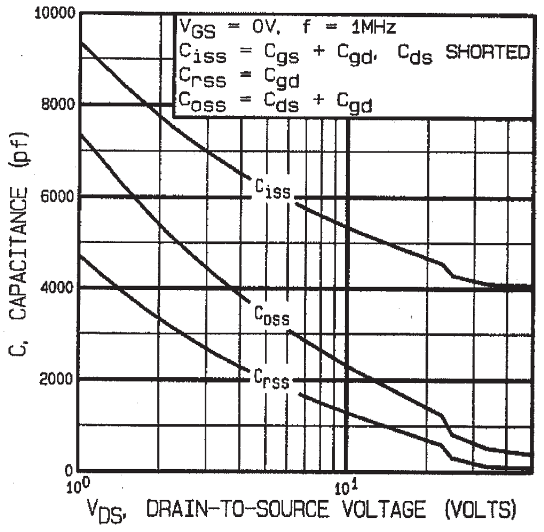


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

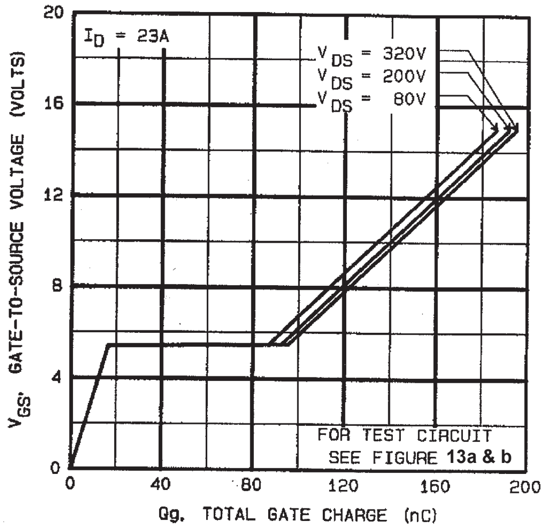


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

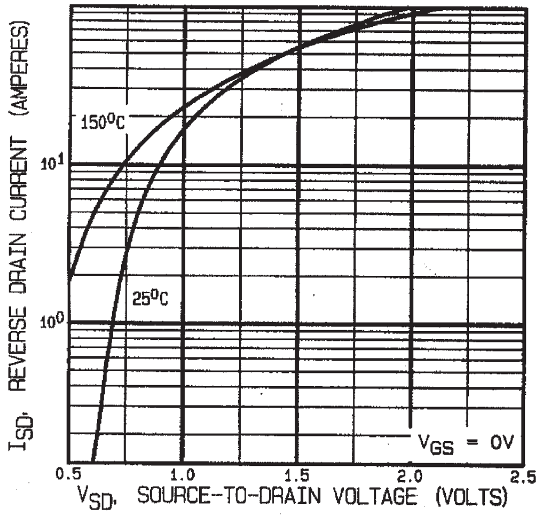


Fig 7. Typical Source-Drain Diode Forward Voltage

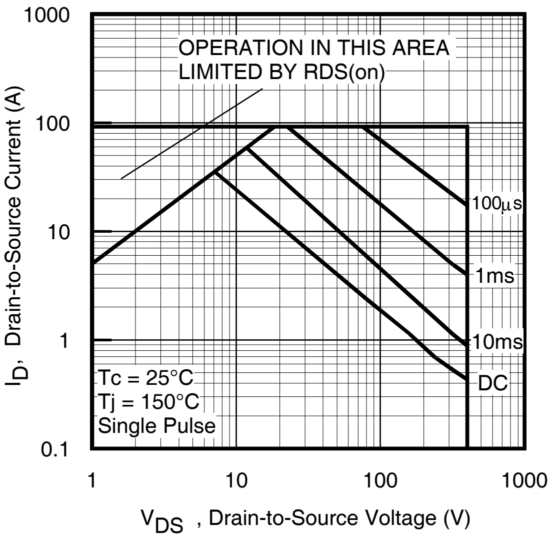


Fig 8. Maximum Safe Operating Area

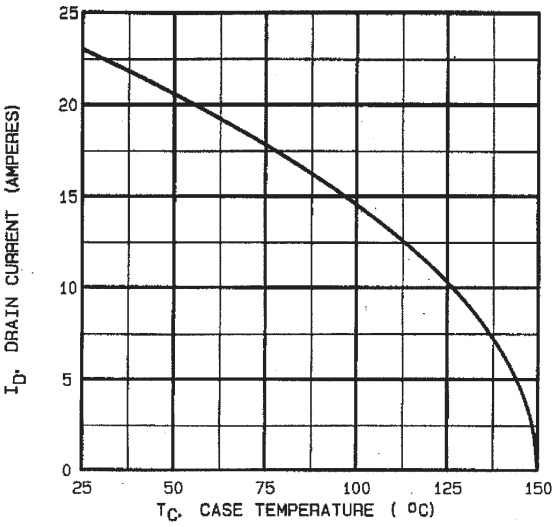


Fig 9. Maximum Drain Current Vs. Case Temperature

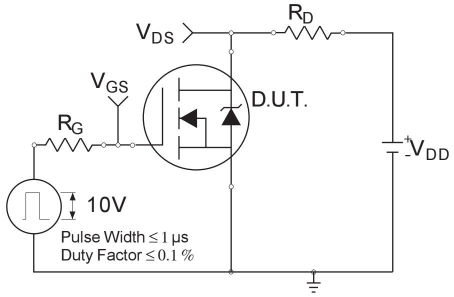


Fig 10a. Switching Time Test Circuit

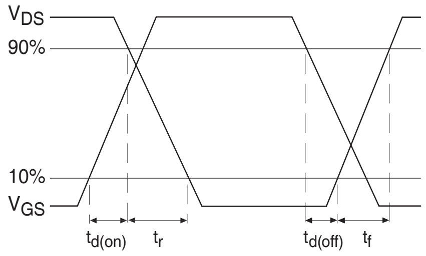


Fig 10b. Switching Time Waveforms

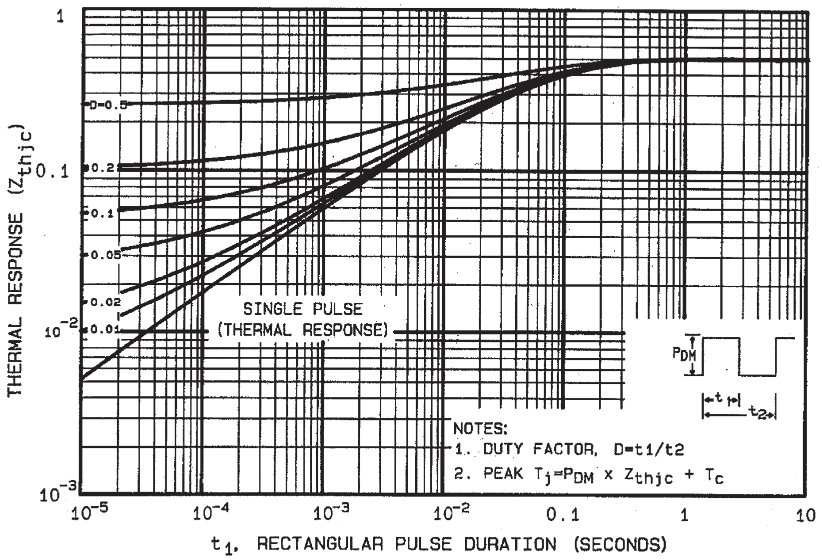


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

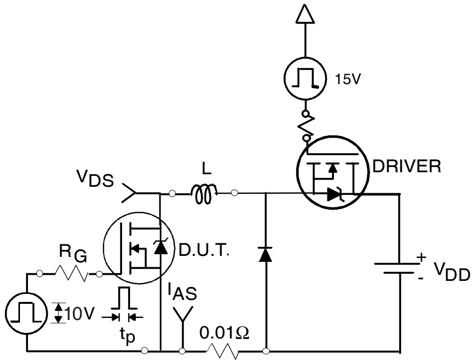


Fig 12a. Unclamped Inductive Test Circuit

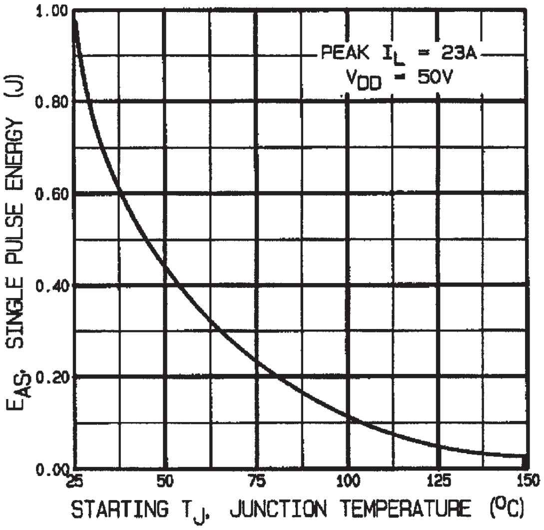


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

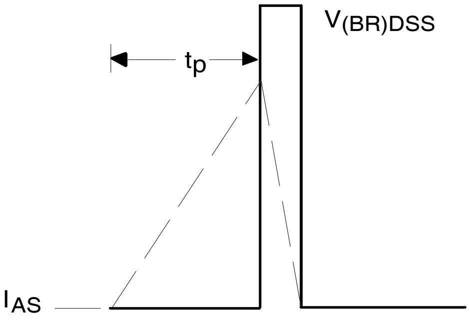
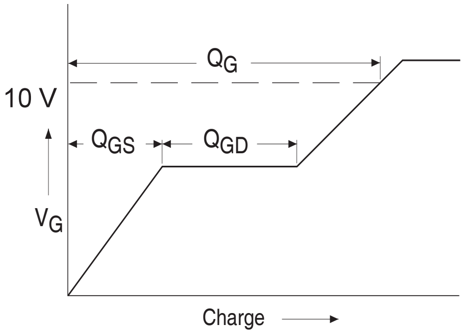


Fig 12b. Unclamped Inductive Waveforms



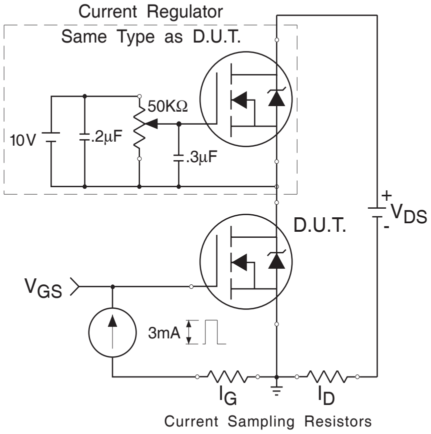


Fig 13a. Basic Gate Charge Waveform

Fig 13b. Gate Charge Test Circuit

Footnotes:

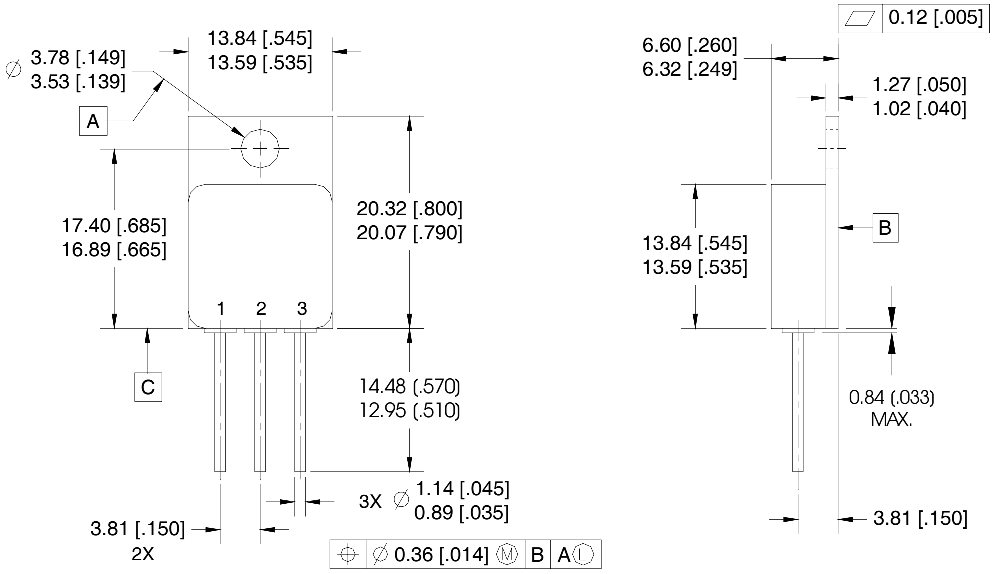
① Repetitive Rating; Pulse width limited by maximum junction temperature.

② V_{DD} = 50V, starting T_J = 25°C, L= 3.7mH
Peak I_L = 23A, V_{GS} = 10V

③ $I_{SD} \leq 23A$, di/dt ≤ 170A/µs,
$V_{DD} \leq 400V$, $T_J \leq 150°C$

④ Pulse width ≤ 300 µs; Duty Cycle ≤ 2%

Case Outline and Dimensions — TO-254AA



NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. CONTROLLING DIMENSION: INCH.
4. CONFORMS TO JEDEC OUTLINE TO-254AA.

PIN ASSIGNMENTS
1 = DRAIN
2 = SOURCE
3 = GATE

CAUTION

BERYLLIA WARNING PER MIL-PRF-19500

Package containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.

International
IOR Rectifier

IR WORLD HEADQUARTERS: 101 N. Sepulveda Blvd. El Segundo, California 90245, USA Tel: (310) 252-7105
IR LEOMINSTER : 205 Crawford St., Leominster, Massachusetts 01453, USA Tel: (978) 534-5776
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